## **AMENDMENTS TO THE SPECIFICATION**

Please amend the specification as follows:

On page 1, amend the title as follows:

## METHOD OF PROVIDING MULTIPLE

## LOGICAL BITS PER MEMORY CELL IN A MEMORY DEVICE

On page 1, amend  $\P$  [0001] as follows:

[0001] This application is a divisional of U.S. Patent Application Serial No. 10/120,113 filed April 9, 2002, now U.S. Patent No. 6,625,055.

On page 12, amend ¶ [0038] as follows:

[0038] The first layer 602 is formed on a substrate layer [[616]] <u>516</u> of the semiconductor device 600. The substrate layer 616 can be any construction of semiconductive material that is a supporting structure for the device 600. Each additional layer of the device 600 is formed on the preceding layer. For example, layer 604 is formed over layer 602, and layer 606 is formed over layer 604. Although the semiconductor device 600 is shown with only three layers, those skilled in the art will appreciate that the device can be fabricated with any number of layers, and with any number of memory cells per layer.

On pages 14-15, amend  $\P$  [0045] as follows:

[0045] At block 708, an electrically insulating material is formed over the first layer to insulate the first layer from any additional layers of the multi-level ROM device. At block 710, columns of conductive material are formed on the insulating layer. At block 712, memory components are formed on the columns of conductive material. At block 714, rows of conductive material are formed over the memory components such that the rows of conductive material cross over the columns of conductive material formed at block 710. Blocks [[608]] 708 through [[614]] 714 are repeated for each additional layer of the memory device, such that each additional layer is formed on a preceding layer.

On page 15, amend  $\P$  [0048] as follows:

[0048] If the memory components formed at blocks [[604]] 704 and [[612]] 712 or [[616]] 716 are formed with an electrically resistive material that is light or heat sensitive, the memory components can be programmed by exposing them to varying degrees of heat or light at block 720.